Silicon NPN Power Transistors

2SD2058

DESCRIPTION

- ·With TO-220F package
- ·Complement to type 2SB1366
- ·Low collector saturation voltage:
- $V_{CE(SAT)}$ =1.0V(Max) at I_C =2A, I_B =0.2A
- ·Collector power dissipation:

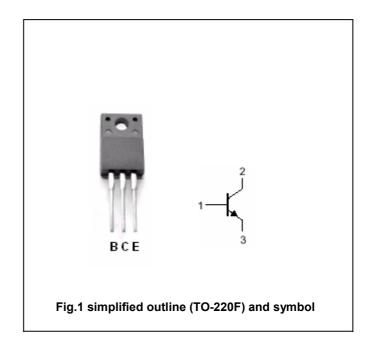
 $P_C=25W(T_C=25\Box)$

APPLICATIONS

·With general purpose applications

PINNING

PIN	DESCRIPTION	
1	Base	
2	Collector	
3	Emitter	



Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
V_{CBO}	Collector-base voltage	Open emitter	60	V	
V _{CEO}	Collector-emitter voltage	Open base	60	V	
V _{EBO}	Emitter-base voltage	Open collector	7	V	
Ic	Collector current		3	А	
I _B	Base current		0.5	Α	
P _C	Collector dissipation	T _a =25□	1.5	W	
		T _C =25□	25		
Tj	Junction temperature		150		
T _{stg}	Storage temperature		-55~150		

SavantIC Semiconductor

Silicon NPN Power Transistors

2SD2058

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA ;I _B =0	60			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2A ;I _B =0.2A			1.5	V
V_{BE}	Base-emitter on voltage	I _C =0.5A;V _{CE} =5V		3.0		V
I _{CBO}	Collector cut-off current	V _{CB} =60V;I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			1.0	mA
h _{FE}	DC current gain	I _C =0.5A; V _{CE} =5V	60			
f _T	Transition frequency	I _C =0.5A; V _{CE} =5V		3.0		MHz
Сов	Collector output capacitance	f=1MHz;V _{CB} =10V		35		pF
Switching times						
t _{on}	Turn-on time			0.65		μs
ts	Storage time	I _C =2.0A; I _{B1} =-I _{B2} =0.2A V _{CC} =30V ,R _L =15Ω		1.30		μs
t _f	Fall time			0.65		μs

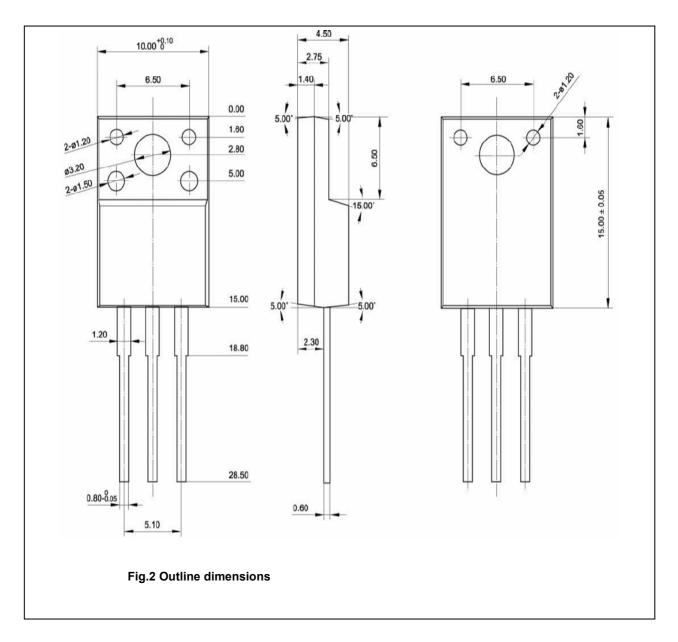
♦ h_{FE} Classifications

0	Y	G
60-120	100-200	150-300

Silicon NPN Power Transistors

2SD2058

PACKAGE OUTLINE



Silicon NPN Power Transistors

2SD2058

